# Notification about the transfer of the semiconductor business

The semiconductor business of Panasonic Corporation was transferred on September 1, 2020 to Nuvoton Technology Corporation (hereinafter referred to as "Nuvoton"). Accordingly, Panasonic Semiconductor Solutions Co., Ltd. became under the umbrella of the Nuvoton Group, with the new name of Nuvoton Technology Corporation Japan (hereinafter referred to as "NTCJ").

In accordance with this transfer, semiconductor products will be handled as NTCJ-made products after September 1, 2020. However, such products will be continuously sold through Panasonic Corporation.

Publisher of this Document is NTCJ.

If you would find description "Panasonic" or "Panasonic semiconductor solutions", please replace it with NTCJ.

\* Except below description page

"Request for your special attention and precautions in using the technical information and semiconductors described in this book"

Nuvoton Technology Corporation Japan



FC694309ER

## MOS FET FC694309ER

Dual N-channel MOSFET

### For switching circuits

#### Features

- Low drive voltage : 1.5 V drive
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL : Level 1 compliant)
- Marking Symbol : X9

#### Basic Part Number

• Dual FK330309 (Individual)

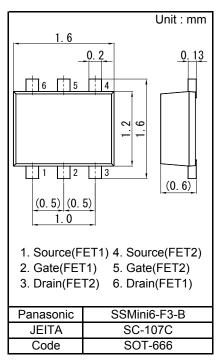
#### Packaging

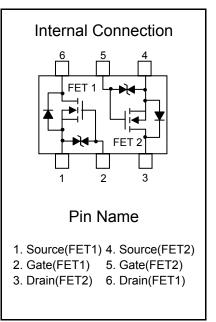
Embossed type (Thermo-compression sealing): 8 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

Parameter		Rating	Unit	
Drain to Source Voltage	VDS	30	V	
Gate to Source Voltage	VGS	±6	V	
Drain Current	ID	100	mA	
Drain Current (Pulsed) *1	IDp	200	mA	
Total Power Dissipation	PD	125	mW	
Channel Temperature	Tch	150	°C	
Storage Temperature Range	Tstg	-55 to +150	С°	
	Drain to Source Voltage Gate to Source Voltage Drain Current Drain Current (Pulsed) <sup>*1</sup> Total Power Dissipation Channel Temperature	Drain to Source VoltageVDSGate to Source VoltageVGSDrain CurrentIDDrain Current (Pulsed) *1IDpTotal Power DissipationPDChannel TemperatureTch	Drain to Source VoltageVDS30Gate to Source VoltageVGS±6Drain CurrentID100Drain Current (Pulsed) *1IDp200Total Power DissipationPD125Channel TemperatureTch150	

Note \*1 Pulse test: Ensure that the channel temperature does not exceed 150 °C







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# ■ Electrical Characteristics Ta = 25 °C ± 3 °C

FET1, FET2

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = 1 mA, VGS = 0 V	30			V
Zero Gate Voltage Drain Current	IDSS	VDS = 30 V, VGS = 0 V			10	μA
Gate-source Leakage Current	IGSS	$VGS = \pm 6 V, VDS = 0 V$			±10	μA
Gate-source Threshold Voltage	Vth	ID = 1 mA, VDS = 10 V	0.3		1.3	V
Drain-source On-state Resistance	RDS(on)1	ID = 10 mA, VGS = 2.5 V		1	4	Ω
	RDS(on)2	ID = 10 mA, VGS = 1.5 V		4	12	
Input Capacitance	Ciss	VDS = 10 V, VGS = 0 V		13		pF
Output Capacitance	Coss	f = 1 MHz		7		
Reverse Transfer Capacitance	Crss			4		
Turn-on Delay Time <sup>*1</sup>	ton	VDD = 3 V, VGS = 0 to 3 V ID = 10 mA, RL = 300 Ω		20		ns
Turn-off Delay Time <sup>*1</sup>	toff	VDD = 3 V, VGS = 3 to 0 V ID = 10 mA, RL = 300 Ω		100		ns

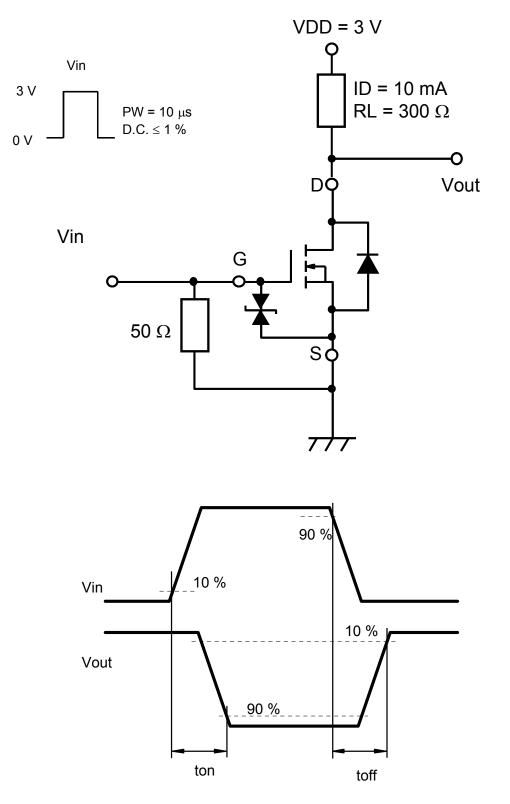
Note : 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

2. \*1 Measurement circuit for Turn-on Delay Time / Turn-off Delay Time

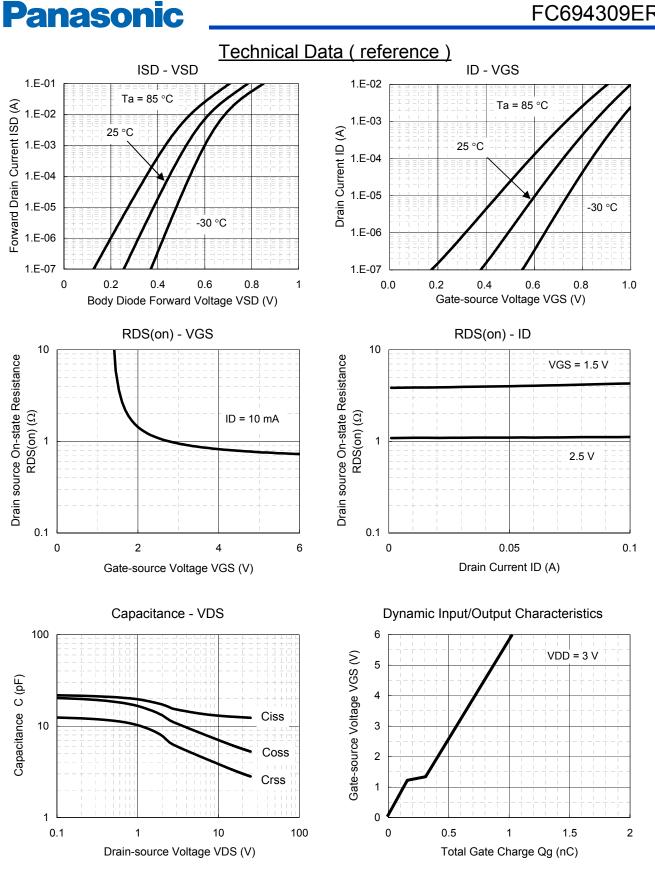


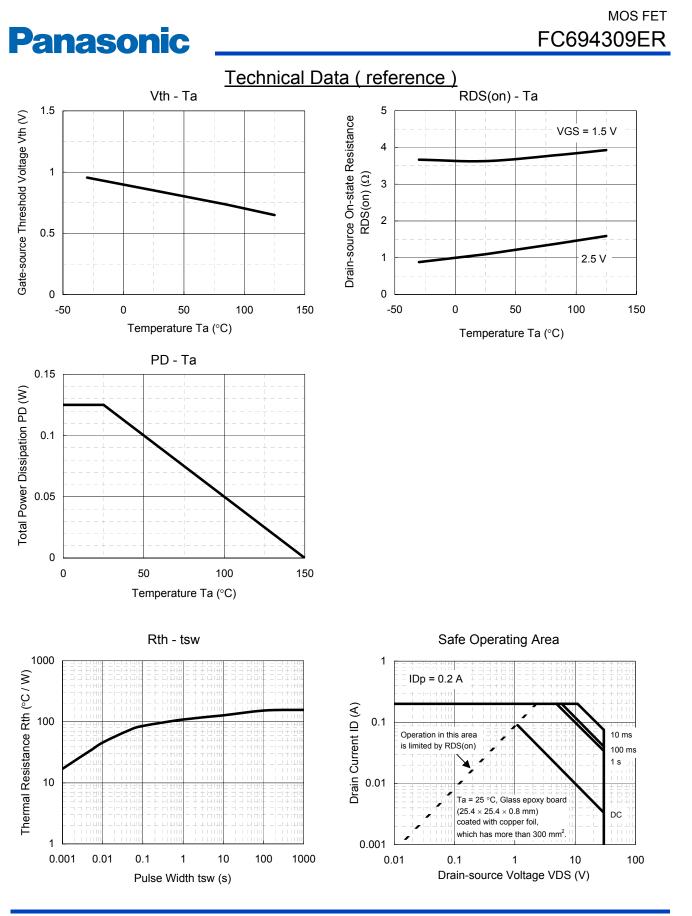
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\*1 Measurement circuit for Turn-on Delay Time / Turn-off Delay Time



### MOS FET FC694309ER

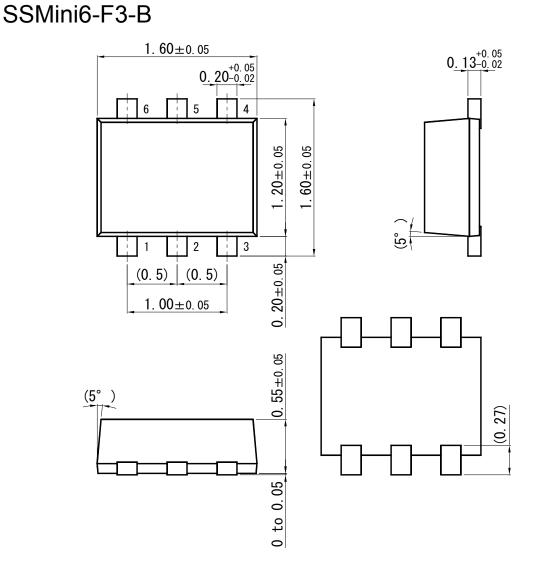




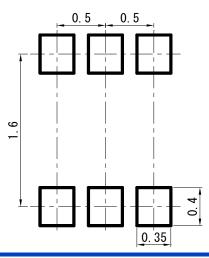


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Unit : mm



■ Land Pattern (Reference) (Unit : mm)



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